Product Summary

BV_{DSS}	$R_{D1D2\ MAX}$	I_D $T_A = +25°C$
-20V	90mΩ @ V_{GS} = -4.5V	-3.2A
	120mΩ @ V_{GS} = -2.5V	-2.7A

Features

- PCB Footprint of 4mm²
- Low On-Resistance
- Low Input Capacitance
- Low Profile, 0.6mm maximum Height
- **ESD Protected Gate**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/**

Description and Applications

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) yet maintain superior switching performance, which makes it ideal for high-efficiency power-management applications.

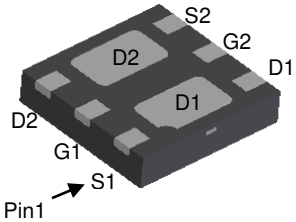
- Load switches
- Power-management functions
- Portable power adaptors

Mechanical Data

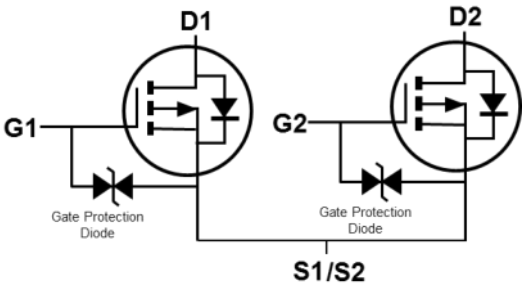
- Package: U-DFN2020-6
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e4
- Terminals Connections: See Diagram Below
- Weight: 0.0065 grams (Approximate)

ESD protected Gate

U-DFN2020-6 (Type B)



Bottom View



Internal Schematic

Ordering Information (Note 4)

Orderable Part Number	Package	Packing	
		Qty.	Carrier
DMP2090UFDB-7	U-DFN2020-6 (Type B)	3000	Tape & Reel
DMP2090UFDB-13	U-DFN2020-6 (Type B)	10,000	Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

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Marking Information

Site 1:

E4 = Product Type Marking Code
YM = Date Code Marking
Y = Year (ex: M = 2025)
M = Month (ex: 9 = September)

Date Code Key

Year	2019	-	2025	2026	2027	2028	2029	2030	2031	2032	2033	2034
Code	G	-	M	N	P	R	S	T	U	V	W	X

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Site 2:

E4 = Product Type Marking Code
YWX = Date Code Marking
Y = Year (ex: 5 = 2025)
W = Week (ex: a = Week 27; z Represents Week 52 and 53)
X = Internal Code (ex: U = Monday)

Date Code Key

Year	2019	-	2025	2026	2027	2028	2029	2030	2031	2032	2033	2034
Code	9	-	5	6	7	8	9	0	1	2	3	4

Week	1-26	27-52	53
Code	A-Z	a-z	z

Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat
Code	T	U	V	W	X	Y	Z

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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-20	V
Gate-Source Voltage			V_{GSS}	±8	V
Continuous Drain Current (Note 6) V_{GS} = -4.5V	Steady State	T_A = +25°C T_A = +70°C	I_D	-3.2 -2.5	A
Maximum Continuous Body Diode Forward Current (Note 6)			I_S	-1.9	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	-22	A
Avalanche Current (Note 7) L = 0.1mH			I_{AS}	-11	A
Avalanche Energy (Note 7) L = 0.1mH			E_{AS}	7	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T_A = +25°C	P_D	0.79	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	159	°C/W
Total Power Dissipation (Note 6)	T_A = +25°C	P_D	1.39	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	90	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	-20	—	—	V	V_{GS} = 0V, I_D = -250µA
Zero Gate Voltage Drain Current, T_J = +25°C	I_{DSS}	—	—	-1.0	µA	V_{DS} = -20V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±10	µA	V_{GS} = ±8V, V_{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(TH)}$	-0.3	—	-1.0	V	V_{DS} = V_{GS}, I_D = -250µA
Static Drain1-Drain2 On-Resistance	R_{D1D2}	—	37	90	mΩ	V_{GS} = -4.5V, I_D = -4A
		—	50	120		V_{GS} = -2.5V, I_D = -3.5A
Diode Forward Voltage	V_{SD}	—	-0.7	-1.2	V	V_{GS} = 0V, I_S = -1.0A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	—	634	—	pF	V_{DS} = -10V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	—	81	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	66	—	pF	
Gate Resistance	R_g	—	20	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (V_{GS} = -4.5V)	Q_g	—	6.8	—	nC	V_{DS} = -4.5V, I_D = -4A, V_{DS} = -10V
Gate-Source Charge	Q_{gs}	—	0.7	—	nC	
Gate-Drain Charge	Q_{gd}	—	1.6	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	4.2	—	ns	V_{DS} = -10V, V_{GS} = -4.5V, R_L = 3.3Ω, R_g = 1Ω
Turn-On Rise Time	t_R	—	3.4	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	23	—	ns	
Turn-Off Fall Time	t_F	—	9.6	—	ns	
Body Diode Reverse-Recovery Time	t_{RR}	—	1.8	—	ns	I_S = -1.0A, dI/dt = 100A/µs
Body Diode Reverse-Recovery Charge	Q_{RR}	—	9.4	—	nC	I_S = -1.0A, dI/dt = 100A/µs

Notes:
5. Device mounted on FR-4 substrate PCB, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PCB, 2oz copper, with 1inch square copper plate.
7. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.

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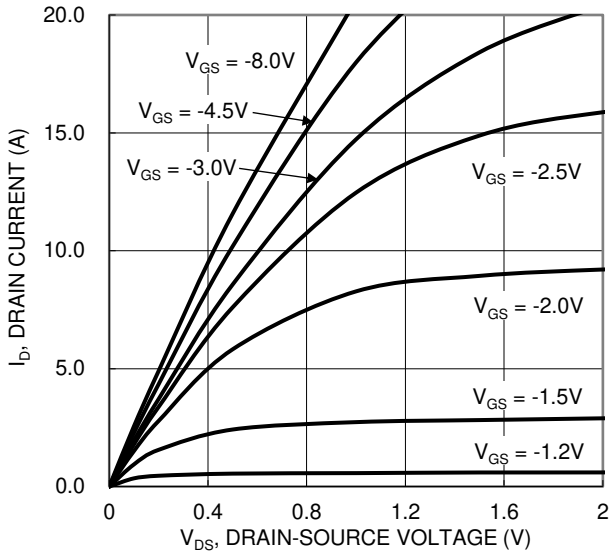

Figure 1. Typical Output Characteristic

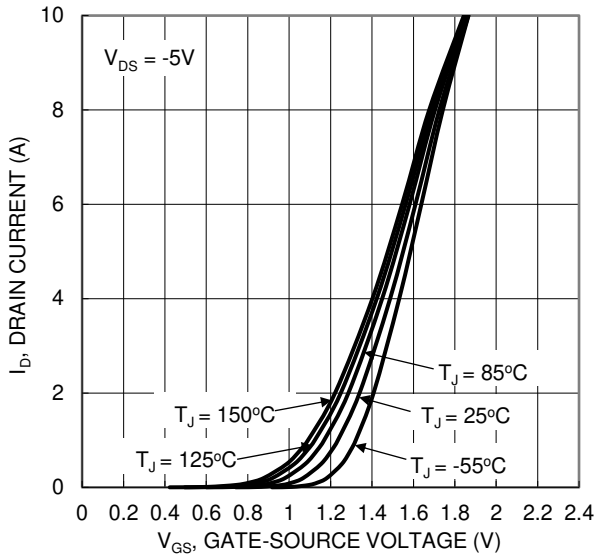

Figure 2. Typical Transfer Characteristic

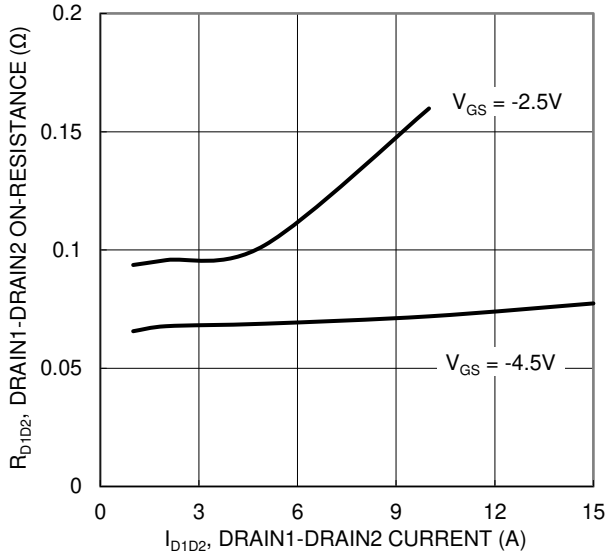

Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

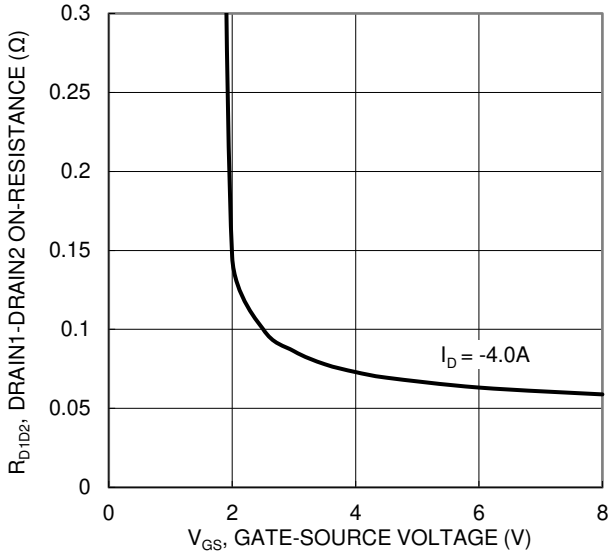

Figure 4. Typical Transfer Characteristic

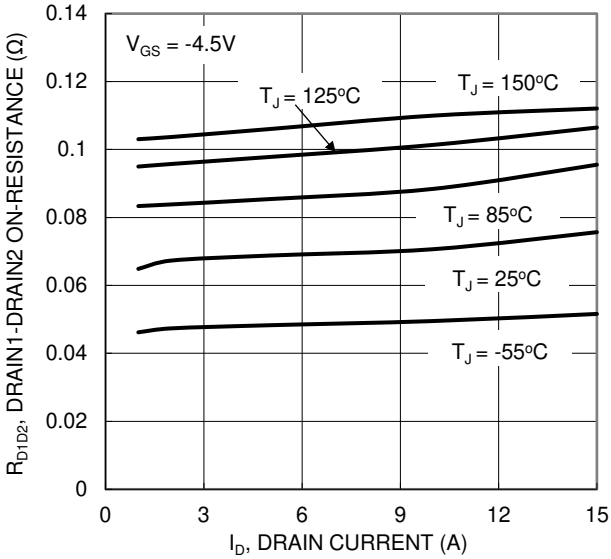

Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

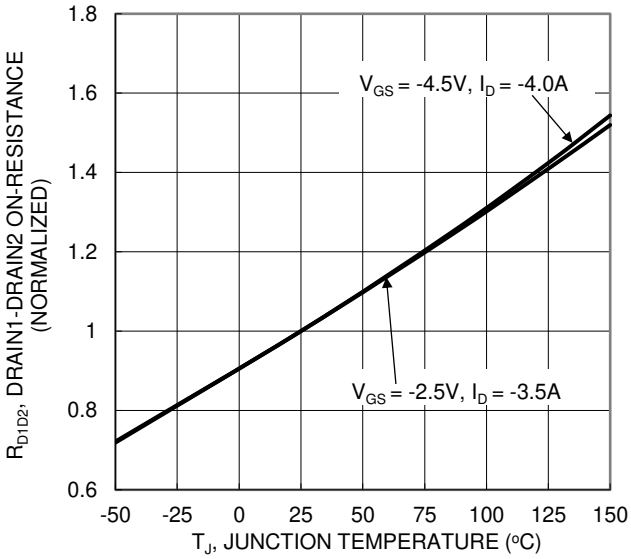

Figure 6. On-Resistance Variation with Junction Temperature

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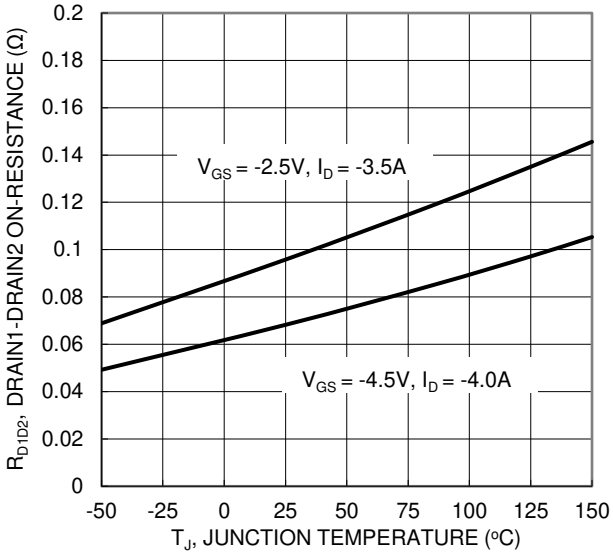

Figure 7. On-Resistance Variation with Junction Temperature

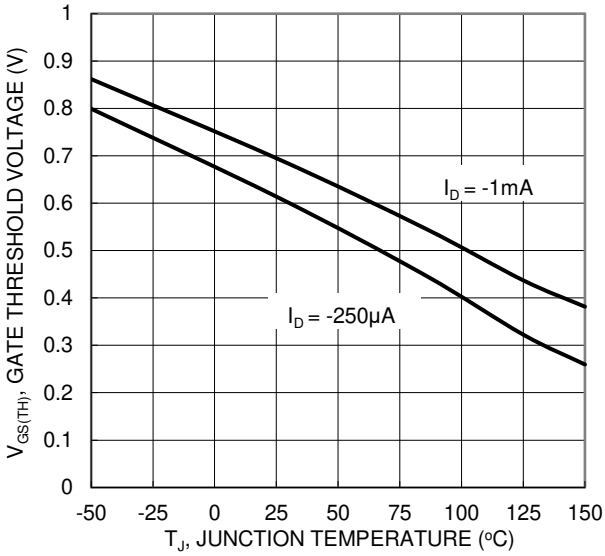

Figure 8. Gate Threshold Variation vs. Junction Temperature

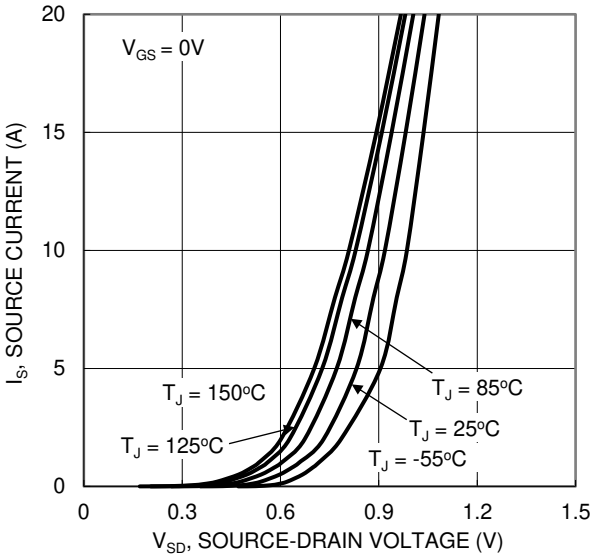

Figure 9. Diode Forward Voltage vs. Current

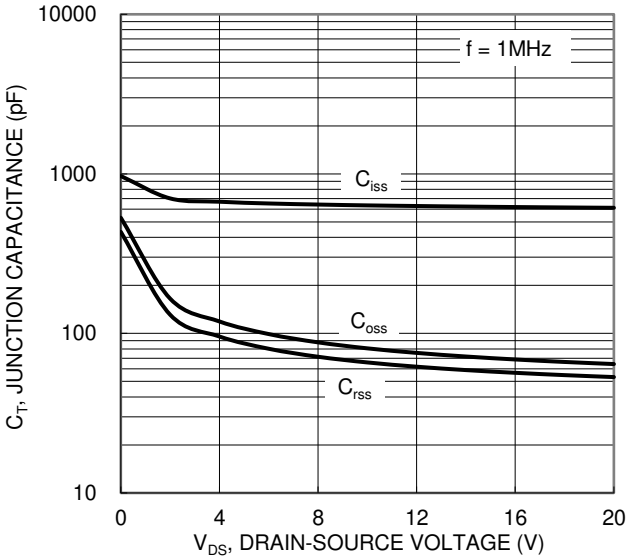

Figure 10. Typical Junction Capacitance

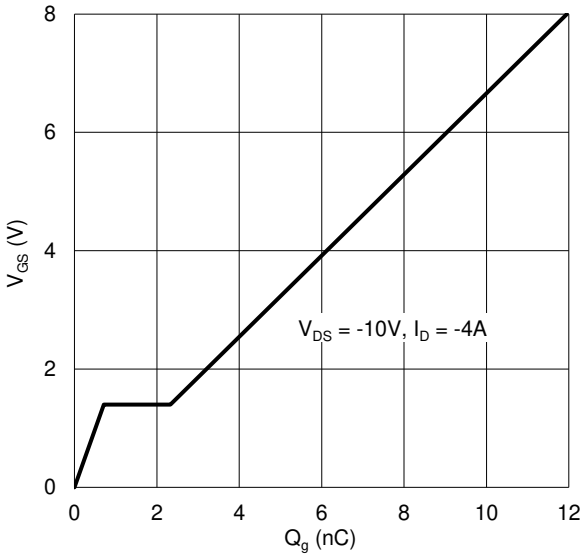

Figure 11. Gate Charge

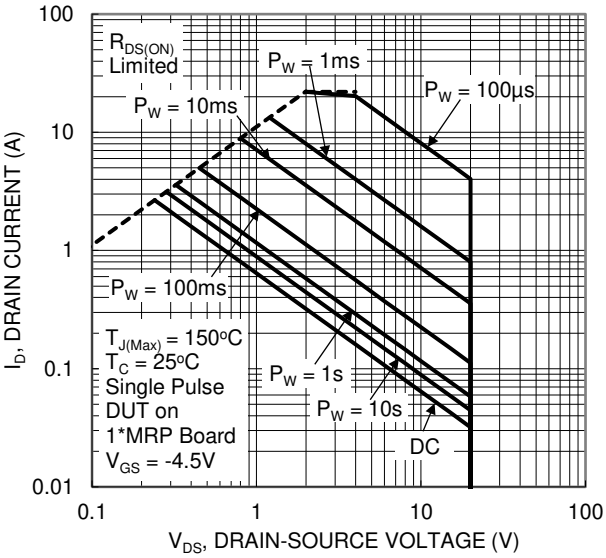

Figure 12. SOA, Safe Operation Area

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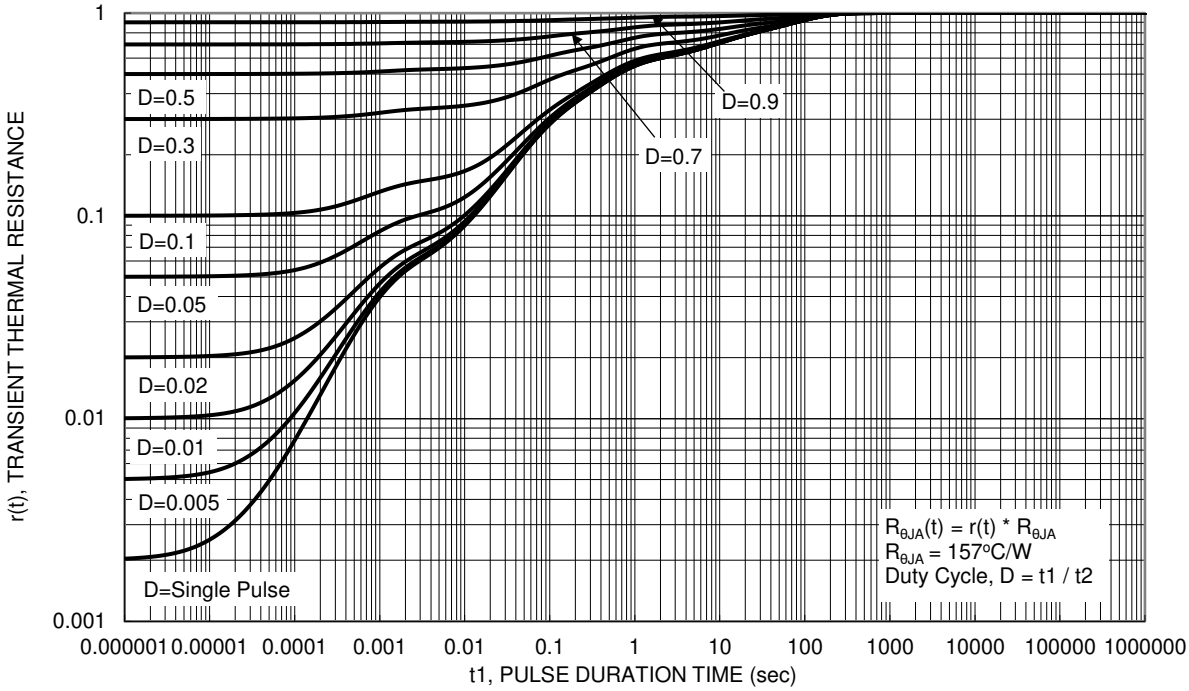

Figure 13. Transient Thermal Resistance

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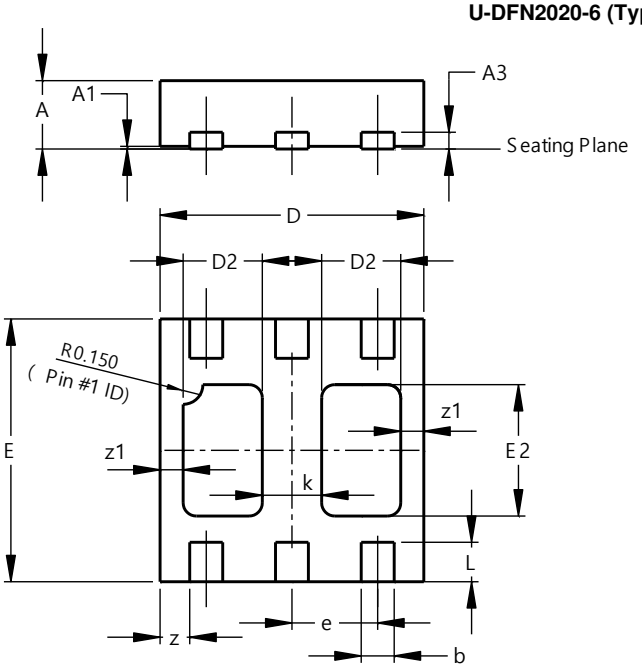
Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type B)

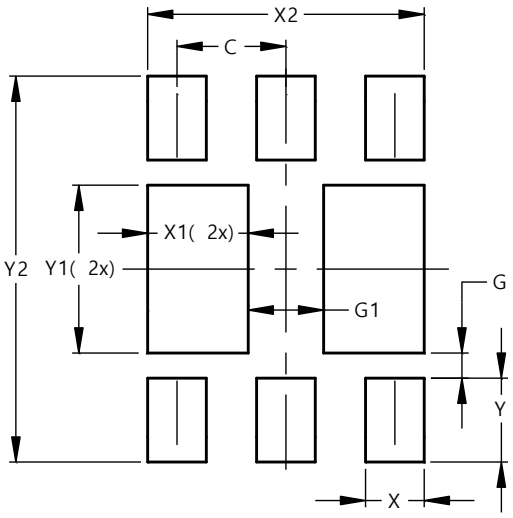


U-DFN2020-6 Type B			
Dim	**Min**	**Max**	**Typ**
A	0.545	0.605	0.575
A1	0.00	0.05	0.02
A3	-	-	0.13
b	0.20	0.30	0.25
D	1.95	2.075	2.00
D2	0.50	0.70	0.60
e	-	-	0.65
E	1.95	2.075	2.00
E2	0.90	1.10	1.00
k	-	-	0.45
L	0.25	0.35	0.30
z	-	-	0.225
z1	-	-	0.175
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type B)



Dimensions	Value (in mm)
C	0.650
G	0.150
G1	0.450
X	0.350
X1	0.600
X2	1.650
Y	0.500
Y1	1.000
Y2	2.300

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